

CY7C1021BN

1-Mbit (64 K × 16) Static RAM

Features

- Temperature ranges
 □ Commercial: 0 °C to 70 °C
 □ Industrial: -40 °C to 85 °C
 □ Automotive-A: -40 °C to 85 °C
 □ Automotive-E: -40 °C to 125 °C
- High speed
 - □ t_{AA} = 15 ns (Automotive)
- Complementary metal oxide semiconductor (CMOS) for optimum speed/power
- Low active power 825 mW (maximum)
- Automatic power down when deselected
- Independent control of upper and lower bits
- Available in Pb-free and non Pb-free 44-pin TSOP II and 44-pin 400-mil-wide SOJ

Functional Description

The CY7C1021BN is a high performance CMOS static RAM organized as 65,536 words by 16 bits. This device has an automatic power down feature that significantly reduces power consumption when deselected.

Writing to the device is accomplished by taking Chip Enable $\overline{(CE)}$ and Write Enable $\overline{(WE)}$ inputs LOW. If Byte Low Enable $\overline{(BLE)}$ is LOW, then data from the input/output (I/O) pins (I/O₁ through I/O₈), is written into the location specified on the address pins (A₀ through A₁₅). If Byte High Enable (BHE) is LOW, then data from I/O pins (I/O₉ through I/O₁₆) is written into the location specified on the address pins (A₀ through A₁₅).

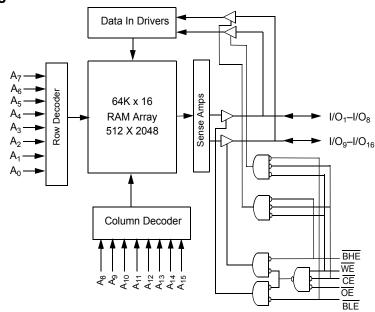
Reading from the device is accomplished by taking \overline{CE} and Output Enable (\overline{OE}) LOW while forcing WE HIGH. If BLE is LOW, then data from the memory location specified by the address pins appears on I/O₁ to I/O₈. If BHE is LOW, then data from memory appears on I/O₉ to I/O₁₆. See the Truth Table on page 11 for a complete description of read and write modes.

The I/O pins (I/O₁ through I/O₁₆) are <u>placed</u> in a high impedance state when the device is <u>deselected</u> (\overline{CE} HIGH), the <u>outputs</u> are disabled (\overline{OE} HIGH), the BHE and <u>BLE</u> are disabled (BHE, BLE HIGH), or during a write operation (\overline{CE} LOW, WE LOW).

The CY7C1021BN is available in standard 44-pin TSOP type II and 44-pin 400-mil-wide SOJ packages. Use part number CY7C1021BN when ordering 15 ns t_{AA} .

For a complete list of related resources, click here.

Logic Block Diagram



Cypress Semiconductor Corporation Document Number: 001-06494 Rev. *J 198 Champion Court

San Jose, CA 95134-1709 • 408-943-2600 Revised November 29, 2017



Contents

Selection Guide	3
Pin Configuration	3
Pin Definitions	
Maximum Ratings	5
Operating Range	5
Electrical Characteristics	5
Capacitance	6
Thermal Resistance	6
AC Test Loads and Waveforms	6
Switching Characteristics	7
Switching Waveforms	
Truth Table	
Ordering Information	
Ordering Code Definitions	

Package Diagrams	13
Acronyms	14
Document Conventions	14
Units of Measure	14
Document History Page	15
Sales, Solutions, and Legal Information	16
Worldwide Sales and Design Support	16
Products	16
PSoC® Solutions	16
Cypress Developer Community	16
Technical Support	16



Selection Guide

Desc	Description		
Maximum access time (ns)		15	
Maximum operating current (mA)	Commercial/Industrial	130	
	Automotive-A	130	
	Automotive-E	130	
Maximum CMOS standby current (mA)	Commercial/Industrial	10	
	Commercial/Industrial (L version)	0.5	
	Automotive-A (L version)	0.5	
	Automotive-E	15	

Pin Configuration

Figure 1.	44-pin	SOJ/TSOP	II	pinout	(Top V	/iew)
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Pin Definitions

Pin Name	Pin Number	I/O Type	Description	
A ₀ -A ₁₅	1–5,18–21, 24–27, 42–44	Input	Address inputs used to select one of the address locations.	
I/O ₁ –I/O ₁₆	7–10, 13–16, 29–32, 35–38	Input/Output	Bidirectional data I/O lines. Used as input or output lines depending on operation.	
NC	22, 23, 28	No Connect	t connected to the die.	
WE	17	Input/Control	Write enable input, active LOW. When selected LOW, a write is conducted. When deselected HIGH, a read is conducted.	
CE	6	Input/Control	Chip enable input, active LOW. When LOW, selects the chip. When HIGH, deselects the chip.	
BHE, BLE	40, 39	Input/Control	Byte enable select inputs, active LOW. $\overline{\text{BHE}}$ controls I/O ₁₆ –I/O ₉ , $\overline{\text{BLE}}$ controls I/O ₈ –I/O ₁ .	
ŌĒ	41	Input/Control	Output enable, active LOW. Controls the direction of the I/O pins. When LOW, the I/O pins are allowed to behave as outputs. When deasserted HIGH, I/O pins are tristated, and act as input data pins.	
V _{SS}	12, 34	Ground	Ground for the device. Should be connected to ground of the system.	
V _{CC}	11, 33	Power Supply	Power supply inputs to the device.	



Maximum Ratings

Exceeding the maximum ratings may impair the useful life of the device. These user guidelines are not tested.

Storage temperature65 °C to +150 °C
Ambient temperature with power applied55 °C to +125 °C
Supply voltage on V_{CC} relative to GND $^{[1]}$ 0.5 V to +7.0 V
DC voltage applied to outputs in High Z state $^{[1]}$ 0.5 V to V_{CC} + 0.5 V
DC input voltage ^[1] –0.5 V to V_{CC} + 0.5 V

Current into outputs (LOW) 20 mA	
Static discharge voltage	
(per MIL-STD-883, Method 3015)> 2001 V	
Latch-up current> 200 mA	

Operating Range

Range	Ambient Temperature (T _A) ^[2]	V _{cc}
Commercial	0 °C to +70 °C	$5 \text{ V} \pm 10\%$
Industrial	–40 °C to +85 °C	
Automotive-A	–40 °C to +85 °C	
Automotive-E	–40 °C to +125 °C	

Electrical Characteristics

Over the operating range

Parameter	Description	Teet (Conditions	-*	15	Unit
Parameter	Description	Test	Jonations	Min	Max	Unit
V _{OH}	Output HIGH voltage	$V_{\rm CC}$ = Min, $I_{\rm OH}$ = -4.0	$V_{\rm CC}$ = Min, $I_{\rm OH}$ = -4.0 mA		-	V
V _{OL}	Output LOW voltage	V _{CC} = Min, I _{OL} = 8.0 m	A	-	0.4	V
V _{IH}	Input HIGH voltage			2.2	6.0	V
V _{IL}	Input LOW voltage ^[1]			-0.5	0.8	V
I _{IX}	Input leakage current	$GND \leq V_I \leq V_{CC}$	Commercial / Industrial	-1	+1	μA
			Automotive-A	-1	+1	μA
			Automotive-E	-4	+4	μA
I _{OZ}	Output leakage current	$GND \leq V_I \leq V_{CC}$,	Commercial / Industrial	-1	+1	μA
		Output Disabled	Automotive-A	-1	+1 μΑ	μA
			Automotive-E	-4	+4	μA
I _{CC}	V _{CC} operating supply current	V _{CC} = Max,	Commercial / Industrial	_	130	mA
		$I_{OUT} = 0 \text{ mA},$ f = f _{MAX} = 1/t _{RC}	Automotive-A	_	130	1
		MAX WRC	Automotive-E	_	130	
I _{SB1}	Automatic CE power down	Max V_{CC} , $\overline{CE} \ge V_{IH}$,	Commercial / Industrial	_	40	mA
	current – TTL inputs	$V_{IN} \ge V_{IH} \text{ or } V_{IN} \le V_{IL},$ f = f _{MAX}	Automotive-A	_	40	1
			Automotive-E	_	50	
I _{SB2}	Automatic CE power down	<u>Ma</u> x V _{CC} ,	Commercial / Industrial	_	10	mA
	current – CMOS inputs	$\overline{CE} \ge V_{CC} - 0.3 V,$ $V_{W} \ge V_{CC} - 0.3 V$	Commercial / Industrial (L)	_	0.5	1
		$V_{IN} \ge V_{CC} - 0.3 V$, or $V_{IN} \le 0.3 V$, f = 0	Automotive-A (L)	-	0.5	
			Automotive-E	_	15	

Notes 1. V_{IL} (min.) = -2.0 V and V_{IH} (max) = V_{CC} + 0.5 V for pulse durations of less than 20 ns. 2. T_A is the "Instant On" case temperature.



Capacitance

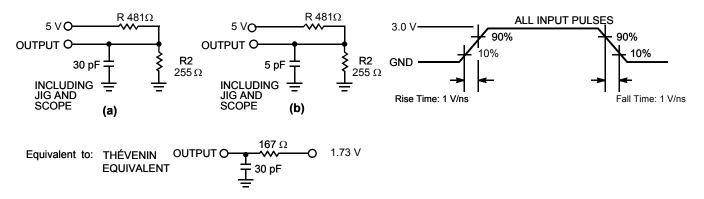
Parameter ^[3]	Description	Test Conditions	Мах	Unit
C _{IN}	Input capacitance	T _A = 25 °C, f = 1 MHz, V _{CC} = 5.0 V	8	pF
C _{OUT}	Output capacitance		8	pF

Thermal Resistance

Parameter ^[3]	Description	Test Conditions	44-pin SOJ	44-pin TSOP II	Unit
Θ_{JA}		Test conditions follow standard test methods and procedures for measuring	64.32	76.89	°C/W
Θ^{JC}	Thermal resistance (junction to case)	thermal impedance, per EIA / JESD51.	31.03	14.28	°C/W

AC Test Loads and Waveforms

Figure 2. AC Test Loads and Waveforms





Switching Characteristics

Over the operating range

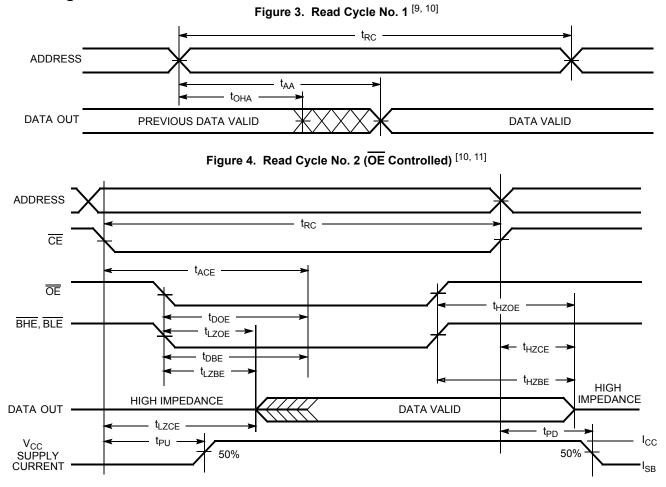
Parameter ^[4]	Description	-1	Unit		
Parameter	Description	Min	Max		
Read Cycle					
t _{RC}	Read cycle time	15	_	ns	
t _{AA}	Address to data valid	-	15	ns	
t _{OHA}	Data hold from address change	3	_	ns	
t _{ACE}	CE LOW to data valid	-	15	ns	
t _{DOE}	OE LOW to data valid	_	7	ns	
t _{LZOE}	OE LOW to low Z ^[4]	0	_	ns	
t _{HZOE}	OE HIGH to high Z ^[5, 6]	_	7	ns	
t _{LZCE}	CE LOW to low Z ^[5]	3	_	ns	
t _{HZCE}	CE HIGH to high Z ^[5, 6]	_	7	ns	
t _{PU}	CE LOW to power up	0	_	ns	
t _{PD}	CE HIGH to power down	_	15	ns	
t _{DBE}	Byte enable to data valid	_	7	ns	
t _{LZBE}	Byte enable to low Z ^[5]	0	_	ns	
t _{HZBE}	Byte disable to high Z ^[5, 6]	_	7	ns	
Write Cycle ^{[7,}	8]			•	
t _{WC}	Write cycle time	15	_	ns	
t _{SCE}	CE LOW to write end	10	_	ns	
t _{AW}	Address setup to write end	10	_	ns	
t _{HA}	Address hold from write end	0	_	ns	
t _{SA}	Address setup to write start	0	_	ns	
t _{PWE}	WE pulse width	12	_	ns	
t _{SD}	Data setup to write end	8	_	ns	
t _{HD}	Data hold from write end	0	_	ns	
t _{LZWE}	WE HIGH to low Z ^[5]	3	_	ns	
t _{HZWE}	WE LOW to high Z ^[5, 6]	_	7	ns	
t _{BW}	Byte enable to write end	9	_	ns	

Notes

- Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5 V, input pulse levels of 0 to 3.0 V, and output loading of the specified I_{OL}/I_{OH} and 30 pF load capacitance.
- 5. At any temperature and voltage condition, t_{HZCE} is less than t_{LZCE} , t_{HZOE} is less than t_{LZOE} , t_{HZBE} is less than t_{LZBE} , and t_{HZWE} is less than t_{LZWE} for any device. 6. t_{HZOE} , t_{HZBE} , t_{HZCE} , and t_{HZWE} are specified with a load capacitance of 5 pF as in part (b) of Figure 2 on page 6. Transition is measured ±500 mV from steady-state voltage.
- 7. The internal write time of the memory is defined by the overlap of CE LOW, WE LOW, and BHE / BLE LOW. CE, WE, and BHE / BLE must be LOW to initiate a write, and the transition of these signals can terminate the write. The input data setup and hold timing should be referenced to the leading edge of the signal that terminates the write.
- 8. The minimum write cycle pulse width for the Write Cycle No. 3 (WE Controlled, OE LOW) should be equal to sum of t_{SD} and t_{HZWE}.



Switching Waveforms



Notes

- 9. <u>Device</u> is continuously selected. \overrightarrow{OE} , \overrightarrow{CE} , \overrightarrow{BHE} , and \overrightarrow{BHE} = V_{IL}. 10. WE is HIGH for read cycle. 11. Address valid prior to or coincident with \overrightarrow{CE} transition LOW.



Switching Waveforms (continued)

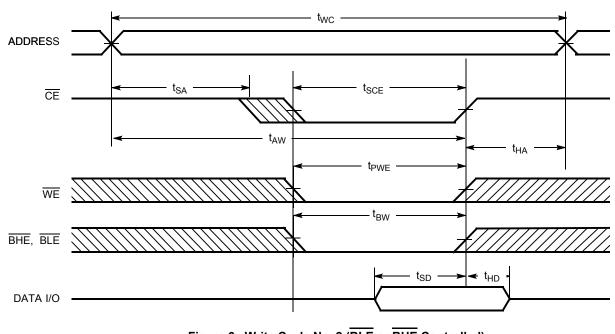
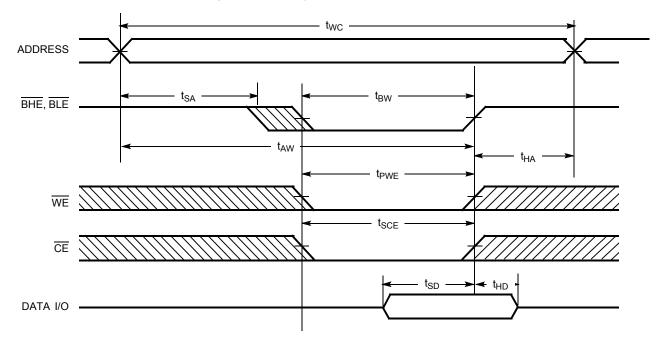


Figure 5. Write Cycle No. 1 (CE Controlled) ^[12, 13]

Figure 6. Write Cycle No. 2 (BLE or BHE Controlled)



Notes

12. Data I/O is high impedance if \overline{OE} or \overline{BHE} and/or \overline{BLE} = V_{IH}. 13. If \overline{CE} goes HIGH simultaneously with \overline{WE} going HIGH, the output remains in a high impedance state.



Switching Waveforms (continued)

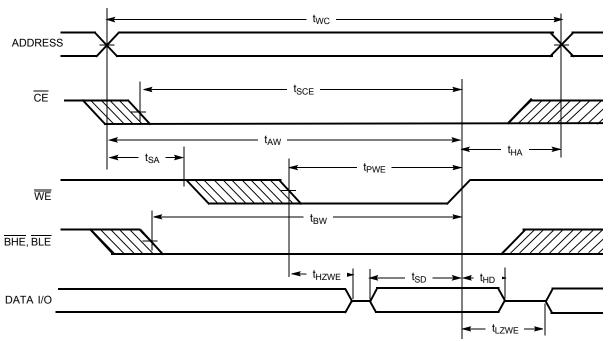


Figure 7. Write Cycle No. 3 (WE Controlled, OE LOW)



Truth Table

CE	OE	WE	BLE	BHE	I/O ₁ –I/O ₈	I/O ₉ –I/O ₁₆	Mode	Power
Н	Х	Х	Х	Х	High Z	High Z	Power down	Standby (I _{SB})
L	L	Н	L	L	Data out	Data out	Read - All bits	Active (I _{CC})
			L	Н	Data out	High Z	Read - Lower bits only	Active (I _{CC})
			Н	L	High Z	Data out	Read - Upper bits only	Active (I _{CC})
L	Х	L	L	L	Data In	Data In	Write - All bits	Active (I _{CC})
			L	Н	Data In	High Z	Write - Lower bits only	Active (I _{CC})
			Н	L	High Z	Data In	Write - Upper bits only	Active (I _{CC})
L	Н	Н	Х	Х	High Z	High Z	Selected, outputs disabled	Active (I _{CC})
L	Х	Х	Н	Н	High Z	High Z	Selected, outputs disabled	Active (I _{CC})



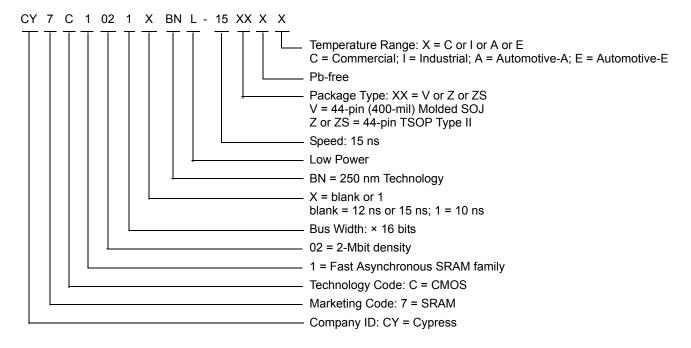
Ordering Information

Cypress offers other versions of this product type in many different configurations and features. The following table contains only the list of parts that are currently available. For a complete listing of all options, refer to the product summary page at http://www.cypress.com/products or contact your local sales representative.

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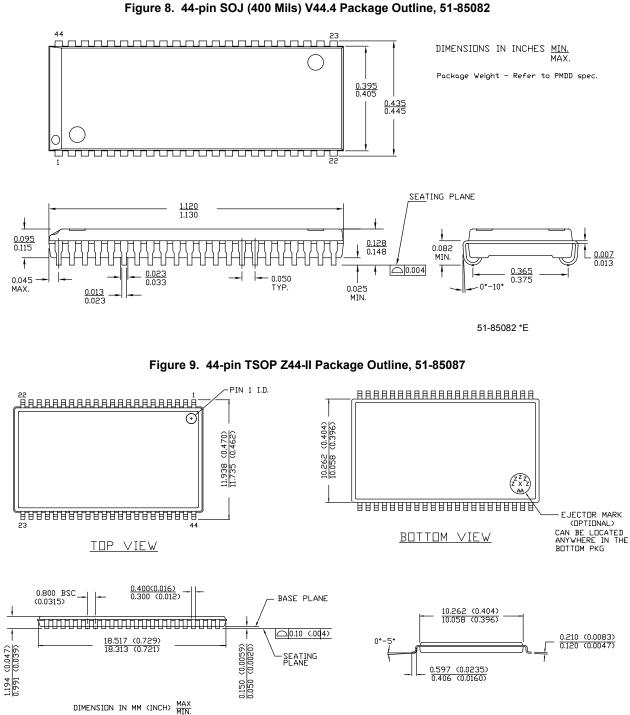
Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
15	CY7C1021BNL-15VXC	51-85082	44-pin (400-mil) Molded SOJ (Pb-free)	Commercial
	CY7C1021BNL-15ZXI	51-85087	44-pin TSOP Type II (Pb-free)	Industrial
	CY7C1021BNL-15ZSXA	51-85087	44-pin TSOP Type II (Pb-free)	Automotive-A
	CY7C1021BN-15ZSXE			Automotive-E

Ordering Code Definitions





Package Diagrams



PKG WEIGHT: REFER TO PMDD SPEC

51-85087 *E



Acronyms

Acronym	Description			
BHE	Byte High Enable			
BLE	Byte Low Enable			
CE	Chip Enable			
CMOS	Complementary Metal Oxide Semiconductor			
I/O	Input/Output			
OE	Output Enable			
SOJ	Small Outline J-lead			
SRAM	Static Random Access Memory			
TSOP	Thin Small Outline Package			
TTL	Transistor-Transistor Logic			
WE	Write Enable			

Document Conventions

Units of Measure

Symbol	Unit of Measure			
°C	degree Celsius			
MHz	megahertz			
μA	microampere			
mA	milliampere			
mm	millimeter			
mW	milliwatt			
ns	nanosecond			
Ω	ohm			
%	percent			
pF	picofarad			
V	volt			
W	watt			



Document History Page

Rev.	ECN No.	Submission Date	Orig. of Change	Description of Change
**	423877	See ECN	NXR	New data sheet.
*A	505726	See ECN	NXR	Removed I _{OS} parameter from DC Electrical Characteristics table. Updated Ordering Information (Added Automotive products).
*В	2897061	03/22/10	AJU	Updated Ordering Information (Removed obsolete parts). Updated Package Diagrams.
*C	2947254	06/08/10	RAME	Updated Pin Definitions (Replaced <u>"Byte write</u> select inputs" with "Byte Enable select inputs" in description of pin BHE, BLE). Updated AC Test Loads and Waveforms (Updated Figure 2 (Added ohm (Ω symbol in Thevenin equivalent circuit)). Updated Switching Characteristics (Updated Note 5 (Included t _{HZBE} and t _{LZB} in the note)). Updated Ordering Information (Included operating range for CY7C1021BNL-15ZXI in ordering information table).
*D	3328634	26/07/2011	AJU	Updated Features (Removed the information associated with speed bins -11 and -12). Removed the note "For best practice recommendations, refer to the Cypres application note, SRAM System Design Guidelines-AN1064." in page 1 and it reference in Functional Description. Updated Functional Description (Removed the information associated with speed bins -10 and -12). Updated Selection Guide (Removed the information associated with speed bins -10 and -12). Updated Electrical Characteristics (Removed the information associated wit speed bins -10 and -12). Updated Switching Characteristics (Removed the information associated wit speed bins -10 and -12). Updated Switching Characteristics (Removed the information associated wit speed bins -10 and -12). Updated Ordering Information. Added Acronyms and Units of Measure. Updated to new template.
*E	4125119	09/16/2013	VINI	Updated Package Diagrams: spec 51-85082 – Changed revision from *C to *E. spec 51-85087 – Changed revision from *C to *E. Updated to new template. Completing Sunset Review.
*F	4545523	10/20/2014	VINI	Updated Document Title to read as "CY7C1021BN, 1-Mbit (64 K × 16) Static RAM". Removed CY7C10211BN related information in all instances across the document. Updated Switching Characteristics: Removed "CY7C1021B" and retained "-15" in column heading "CY7C1021B-15". Added Note 8 and referred the same note in "Write Cycle". Added t _{PWE} parameter and its details. Completing Sunset Review.
*G	4557296	10/31/2014	VINI	Updated Switching Characteristics: Updated minimum and maximum values of t _{PWE} parameter.
*H	4578500	12/16/2014	VINI	Updated Ordering Information: Removed the prune part number CY7C1021BN-15VXE.
*	4984333	10/23/2015	NILE	Updated to new template. Completing Sunset Review.
*J	5979549	11/29/2017	AESATMP9	Updated logo and copyright.



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